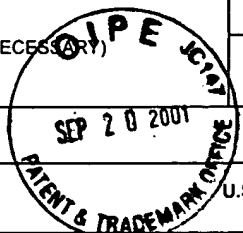


FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMMC.005AUS	APPLICATION NO. 09/887,199
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT RAAJMAKERS et al.	
		FILING DATE June 21, 2001	GROUP 2811



U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
A.M.	1	4,058,430	11/15/77	Suntola et al.	156	611	11/25/75
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FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
A.M	2	WO 96/17107	06.06.96	PCT				
/								
/								

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
A.M.	3	Dücső, C. et al., <i>Research Institute for materials Science – ATKI, H-1525 Budapest, Hungary</i> , Utriainen, M. et al., <i>Laboratory of Inorganic and Analytical Chemistry, Helsinki University of Technology, FIN-02150 Espoo, Finland</i> , "Deposition of Tin Oxide into Porous Silicon by Atomic Layer Epitaxy," <i>J. Electrochemical Society</i> , Vol. 143, No. 2, pp. 683-687 (1996).
/	4	Horike, Y. et al., "Filling of Si oxide into a deep trench using digital CVD method," <i>Applied Surface Science</i> , Vol. 46, pp. 168-174 (1990).
/	5	"SOI Technology: IBM's Next Advance In Chip Design," World wide web address: chips.ibm.com/bluelogic/showcase/soi/soipaper.pdf pp. SOI 1-SOI 10.
/	6	Kaizuke, T. et al., "Conformal Chemical Vapor Deposition TiN(111) Film Formation as an Underlayer of Al for Highly Reliable Interconnects," <i>Jpn. J. Appl. Phys.</i> , Vol. 33, Part 1, No. 1B, pp. 470-474 (1994).
/	7	Kukli, K. et al., "Atomic Layer Epitaxy Growth of Tantalum Oxide Thin Films from Ta(OC ₂ H ₅) ₅ and H ₂ O," <i>J. Electrochem. Soc.</i> , Vol. 142, No. 5, pp. 1670-1674 (1995).
/	8	Lee, William E. D Phil. et al., Department of Engineering Materials and Sorby Centre for Electron Microscopy, Sheffield University, Sheffield, UK., <i>Ceramic Microstructures. Property control by processing</i> , Chapman & Hall publishers, p. 297 (1994).
/	9	Min, Jae-Sik et al., "Atomic Layer Deposition of TiN Thin Films by Sequential Introduction of Ti Precursor and NH ₃ ," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 514, pp. 337-342 (1998).
/	10	Min, Jae-Sik et al., "Atomic Layer Deposition of TiN Films by Alternate Supply of Tetrakis (ethylmethylamino)-Titanium and Ammonia," <i>Jpn. J. Appl. Phys.</i> , Vol. 37, Pt. 1, No. 9A, pp. 4999-5004 (1998).
/	11	Niinistö, L. et al., "synthesis of oxide thin films and overlayers by atomic layer epitaxy for advanced applications," <i>Materials Science and Engineering</i> , Vol. B41, pp. 23-29 (1996).
/	12	Ott, A.W. et al., "Modification of Porous Alumina Membranes Using Al ₂ O ₃ Atomic Layer Controlled Deposition," <i>Chem. Mater.</i> , Vol. 9, No. 3, pp. 707-714 (1997).
/	13	Titala, M. et al., "Atomic Layer Epitaxy Growth of TiN Thin Films from TiI ₄ and NH ₃ ," <i>J. Electrochem. Soc.</i> , Vol. 145, No. 8, pp. 2914-2920 (1998).

EXAMINER	ANH D. MAI	DATE CONSIDERED	10/31/02
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		FILING DATE June 21, 2001	GROUP 2811

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
A.M.	14	Ritala, M. et al., "Coumuncations. Perfectly Conformal TiN and Al ₂ O ₃ Films Deposited by Atomic Layer Deposition," <u>Chemical Vapor Deposition</u> , Vol. 5, No. 1, pp. 7-9 (1999).
	15	Sakaue, H. et al., "Digital Chemical Vapor Deposition of SiO ₂ Using a Repetitive Reaction of Triethylsilane/Hydrogen and Oxidation," <u>Japanese Journal of Applied Physics</u> , Vol. 30, No. 1B, pp. L 124-L 127 (1990).
	16	Sneh, O. et al., "Atomic layer growth of SiO ₂ on Si(100) using SiCl ₄ and H ₂ O in a binary reaction sequence," <u>Surface Science</u> , Vol. 334, pp. 135-152 (1995).
	17	Suntola, T., "Atomic Layer Epitaxy," <u>Handbook of Crystal Growth 3. Thin Films and Epitaxy. Part B: Growth Mechanisms and Dynamics</u> , D.T.J. Hurle editor, Chapter 14, pp. 602-663 (1994).
	18	Wise, M.L. et al., "Diethyldiethoxysilane as a New Precursor for SiO ₂ Growth on Silicon," <u>Mat. Res. Soc. Symp. Proc.</u> , vol. 334, pp. 37-43 (1994).

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